

# **AB081C40W**



### **TECHNICAL DATA**

# High Power Single Bar CW Infrared Laser Diode

#### **Features**

- Output Power: 40 W
- 780-830 nm Emission Wavelength
- Spectral Width: ≤3 nm
- High Reliability, High Efficiency

### **Applications**

- Laser Pumping
- Medical Usage
- Printing

## Specifications (25°C)

| Item                               | Symbol                                     | Value   | Unit  |
|------------------------------------|--|---------|-------|
| Optical Specifications             |  |         |       |
| CW Output Power                    | Po   | 40      | W     |
| Array Length                       | L  | 10      | mm    |
| Center Wavelength                  | λ <sub>C</sub>                             | 780-830 | nm    |
| Wavelength Tolerance               |  | ± 5     | nm    |
| Spectral Width                     | Δλ   | ≤ 3     | nm    |
| Emitting Area                      | WxH  | 150 x 1 | μm    |
| Emitter Pitch                      |  | 500     | μm    |
| Number of Emitters                 |  | 19      |       |
| Wavelength Temperature Coefficient |  | 0.3     | nm/°C |
| Beam Divergence                    | $\theta_{\perp} \times \theta_{\parallel}$ | 40x8    | deg   |
| Electrical Specifications          |  |         |       |
| Slope Efficiency                   | Es   | ≥ 1     | W/A   |
| Conversion Efficiency              | N <sub>S</sub>                             | ≥ 40%   |       |
| Threshold Current                  | I <sub>TH</sub>                            | ≤ 12    | Α     |
| Operating Current                  | I <sub>F</sub>                             | ≤ 50    | Α     |
| Operating Voltage                  | U <sub>F</sub>                             | ≤ 2.2   | V     |
| Absolute Maximum Ratings           |  |         |       |
| Reverse Voltage                    | $U_R$                                      | 2.5     | V     |
| Operating Temperature              | T <sub>OP</sub>                            | +10 +40 | °C    |
| Storage Temperature                | T <sub>STG</sub>                           | -40 +85 | °C    |





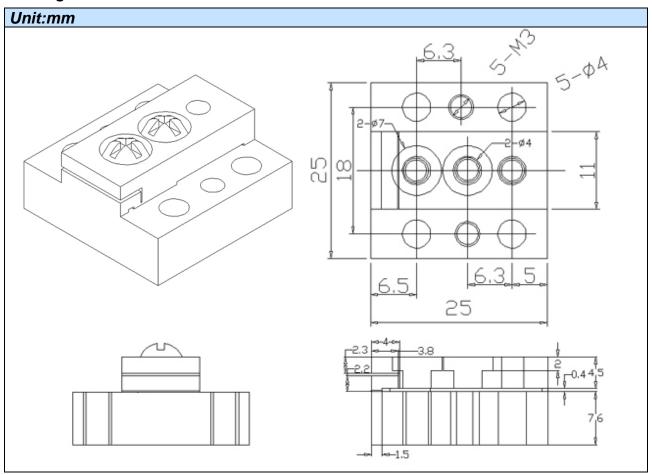
# ROITHNER LASERTECHNIK GIRDH

WIEDNER HAUPTSTRASSE 76

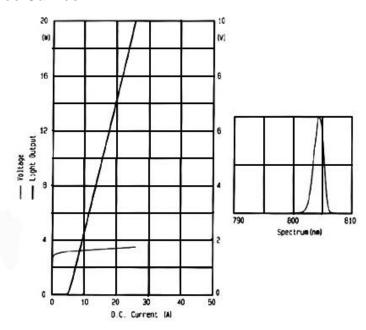
1040 VIENNA TEL. +43 I 586 52 43 -O, FAX. -44, OFFICE@ROITHNER-LASER.COM



## Package Dimensons



## **Typical Performance Curves**





# ROITHNER LASERTECHNIK GMBH

WIEDNER HAUPTSTRASSE 76 IO40 VIENNA AUSTRIA TEL. +43 I 586 52 43 -0, FAX. -44, OFFICE@ROITHNER-LASER.COM



### **Notes**

- 1. High power laser diode arrays are high energy laser devices. It is harmful to human body and health. Never look directly into the laser output port!
- 2. The storage temperature is between -40 and 85 °C.
- 3. In generally, the lifetime can be shortened by high temperature. So the generated heat must be removed in time when the LD is working. The water cooling system, forced air cooling or TEC system are recommended to keeping the LD at a suitable temperature.
- 4. Constant-current power supply with voltage regulator should be used to avoid surge. To use a laser diode in following sequences: Turn on the power supply; connect to the laser diode; increase the current gradually, and then turn off the power. Please make sure that the power supply has no current overshoot at any time. The current overshoot can damage the laser diodes permanently.
- 5. The high power laser diode arrays are very sensitive to electrostatic. Please wear anti-static bracelet during operating with the laser diode arrays.
- 6. Be sure that the operating current does not exceed the specified operating current. Otherwise it will accelerate laser aging, shorten lifetime or even damage devices permanently.
- 7. A clean, dry and ventilated environment should be available when storing and operating laser diode arrays. Dust may degrade the laser diode arrays.